NEW BOOT BLOCK FLASH MEMORY

FLASH MEMORY

MT28F008B5

5V Only

FEATURES

- Eleven erase blocks:
  - 16KB boot block (protected)
  - Two 8KB parameter blocks
  - Eight main memory blocks
- 5V-only operation:
  - 5V ±10% V_{CC}
  - 5V ±10% (12V compatible) V_{PP}
- Extended temperature range option: -40°C to +85°C
- Address access times:
  - 70ns, 90ns
- Automated write and erase algorithm
- Two-cycle WRITE/ERASE sequence

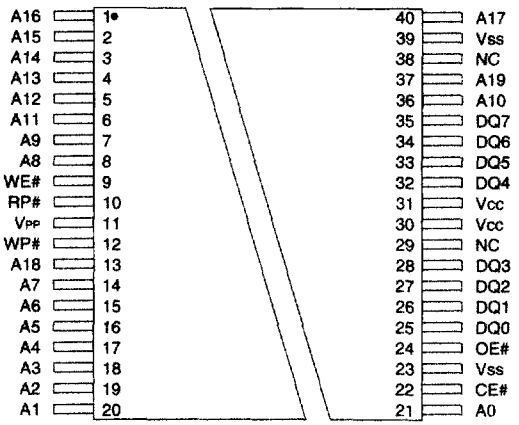
OPTIONS / MARKING

• Timing	
70ns access	-7
90ns access	-9
• Boot Block Starting Address	
Top (FFFFFFH)	T
Bottom (00000H)	B
• Operating Temperature Range	
Commercial (0°C to +70°C)	None
Extended (-40°C to +85°C)	ET
• Package	
Plastic 40-lead TSOP Type 1 (10mm x 20mm)	VG

- Part Number Example: MT28F008B5VG-9 T

PIN ASSIGNMENT (Top View)

40-Pin TSOP Type I
(FB-1)



GENERAL DESCRIPTION

The MT28F008B5 is a nonvolatile, electrically block-erasable (Flash), programmable read-only memory containing 8,388,608 bits organized as 1,048,576 words by 8 bits. Writing or erasing the device is done with a 5V V_{PP} voltage, while all operations are performed with a 5V V_{CC} ($V_{PP} \geq V_{CC}$). It is fabricated with Micron's advanced CMOS floating-gate process.

The MT28F008B5 is organized into eleven separately erasable blocks. To ensure that critical firmware is protected from accidental erasure or overwrite, the MT28F008B5 features a hardware-protected boot block. Writing or erasing the boot block requires either applying a super-voltage to the RP# pin or driving WP# HIGH in addition to executing the normal WRITE or ERASE sequences. This block may be used to store code implemented in low-level system recovery. The remaining blocks vary in density and are written and erased with no additional security measures.

Please refer to Micron's web site (www.micron.com/flash/htmls/datasheets.html) for the latest data sheet revisions.